

National Semiconductor

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LM494 **Pulse Width Modulated Control Circuit**

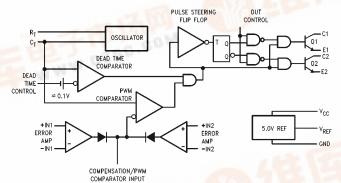
General Description

The LM494 is a monolithic integrated circuit which includes all the necessary building blocks for the design of pulse width modulated (PWM) switching power supplies, including push-pull, bridge and series configurations. The device can operate at switching frequencies between 1.0 kHz and 300 kHz and output voltages up to 40V. The operating temperature range specified for the LM494C is 0°C to 70°C and for the LM494V is -40° C to $+85^{\circ}$ C.

Features

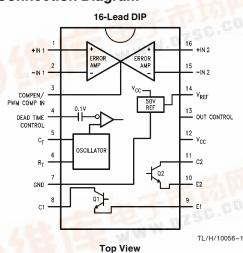
- Uncommitted output transistors capable of 200 mA source or sink
- On-chip error amplifiers
- On-chip 5.0V reference
- \blacksquare Internal protection from double pulsing of outputs with narrow pulse widths or with supply voltages below specified limits
- Dead time control comparator
- Output control selects single ended or push-pull operation
- Easily synchronized (slaved) to other circuits

Block Diagram



TL/H/10056-2

Connection Diagram



Ordering Information

	Device Code	Package Code	Package Description				
	LM494IN	N16A	Molded DIP				
	LM494CJ	J16A	Ceramic DIP				
	LM494CN	N16A	Molded DIP				

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Absolute Maximum Ratings

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature Range

Ceramic DIP -65° C to $+175^{\circ}$ C Molded DIP -65°C to $+150^{\circ}\text{C}$

Operating Temperature Range

Industrial (LM494I) -40°C to +85°C Commercial (LM494C) 0°C to +70°C

Lead Temperature

Ceramic DIP (Soldering, 60 sec.) 300°C Molded DIP (Soldering, 10 sec.) 265°C

Internal Power Dissipation (Notes 1, 2)

16L-Ceramic DIP 1.50W 16L-Molded DIP 1.04W Supply Voltage 42V

Voltage from Any Lead to Ground

(except Lead 8 and Lead 11)

Output Collector Voltage 42V Peak Collector Current (I_{C1} and I_{C2}) 250 mA **ESD Susceptibility** (to be determined)

Recommended Operating Conditions

Power Supply Voltage (V_{CC}) 7.0V to 40V

Voltage on Any Lead

except Leads 8 and 11

(Referenced to Ground) (V_I) -0.3 V to $V_{\hbox{\footnotesize CC}}\,+\,0.3 V$ Output Voltage Collector (V_{C1}, V_{C2}) -0.3V to 40V

Output Collector Current (I_{C1}, I_{C2}) 200 mA Timing Capacitor (C_T) 470 pF to 10 μF Timing Resistor (R_T) 1.8 k Ω to 500 k Ω

Oscillator Frequency (f_{OSC}) 1.0 kHz to 300 kHz

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Electrical Characteristics $T_A = 0$ °C to +70°C for the LM494C, $T_A = -40$ °C to +85°C for the LM494I, $V_{CC} = 15$ V, $t_{OSC} = 10$ kHz, unless otherwise specified

 V_{CC} + 0.3V

Symbol	Parameter	Con	ditions	Min	Тур	Max	Units
REFEREN	CE SECTION						
V _{REF}	Reference Voltage (Note 3)	I _{REF} = 1.0 mA		4.75	5.0	5.25	٧
Reg _{LINE}	Line Regulation of Reference Voltage	$7.0V \le V_{CC} \le 40V$			2.0	25	mV
TCV _{REF}	Temperature Coefficient of Reference Voltage	$0^{\circ}\text{C} \le \text{T}_{\text{A}} \le 70^{\circ}\text{C}$			0.01	0.03	%/°C
Reg _{LOAD}	Load Regulation of Reference Voltage	$1.0 \text{ mA} \le I_{REF} \le 10 \text{ mA}$			1.0	15	mV
los	Output Short Circuit Current	V _{REF} = 0V	$0^{\circ}\text{C} \leq \text{T}_{A} \leq +70^{\circ}\text{C}$	10	35	50	mA
			$-40^{\circ}\text{C} \le T_{A} \le +85^{\circ}\text{C}$		35		
OSCILLAT	OR SECTION						
fosc	Oscillator Frequency (Figure 10)	$C_T = 0.01 \mu F,$ $R_T = 12 k\Omega$			10		kHz
Δf_{OSC}	Oscillator Frequency Change	$C_T = 0.01 \mu F$	$0^{\circ}\text{C} \leq \text{T}_{A} \leq +70^{\circ}\text{C}$			2.0	- %
		$R_T = 12 k\Omega$	$-40^{\circ}\text{C} \le T_{A} \le +85^{\circ}\text{C}$			2.0	/0
DEAD TIM	E CONTROL SECTION						
I _{IB (DT)}	Input Bias Current	$V_{CC} = 15V, 0V \le V_4 \le 5.25V$			-2.0	-10	μΑ
DC _(Max)	Maximum Duty Cycle, Each Output	V _{CC} = 15V, Lead 4 = 0V, Output Control = V _{REF}		45			%
V _{TH(in)}	Input Threshold Voltage	Zero Duty Cycle			3.0	3.3	V
		Maximum Duty Cycle		0			
ERROR A	MPLIFIER SECTIONS						
V_{IO}	Input Offset Voltage	$V_3 = 2.5V$			2.0	10	mV
I _{IO}	Input Offset Current	V ₃ = 2.5V			25	250	nA
I _{IB}	Input Bias Current	V ₃ = 2.5V			0.2	1.0	μΑ
V _{ICR}	Input Common Mode Voltage Range	$7.0V \le V_{CC} \le 40V$		-0.3		V _{CC}	V
A _{VS}	Large Signal Voltage Gain	$0.5 V \leq V_3 \leq 3.5 V$		60	74		dB
BW	Bandwidth				650		kHz

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Symbol	Parameter	Conditions		Min	Тур	Max	Units
PWM CO	MPARATOR SECTION (Figure 9)						
V _{THI}	Inhibit Threshold Voltage	Zero Duty Cycle			4.0	4.5	٧
I _O -	Output Sink Current (Note 4)	$0.5V \le V_3 \le 3.5V$		-0.2	-0.6		mA
I _O +	Output Source Current (Note 4)	$0.5V \le V_3 \le 3.5V$		2.0			mA
OUTPUT	SECTION						
V _{CE(sat)}	Output Saturation Voltage Common Emitter Configuration (Figure 3)	$V_E = 0V$, $I_C = 200 \text{ mA}$	$ \begin{array}{c} 0^{\circ}C \leq T_{A} \leq +70^{\circ}C \\ -40^{\circ}C \leq T_{A} \leq +85^{\circ}C \end{array} $		1.1	1.3	V
	Emitter Follower Configuration (Figure 4)	$V_C = 15V, I_E = 200 \text{ mA}$			1.5	2.5	
I _{C(off)}	Collector Off-State Current	V _{CC} = 40V, V _{CE} = 40V			2.0	100	μΑ
I _{E(off)}	Emitter Off-State Current	$V_{CC} = V_C = 40V,$ $V_E = 0$	$ \begin{array}{c} 0^{\circ}C \leq T_{A} \leq +70^{\circ}C, \\ -40^{\circ}C \leq T_{A} \leq +85^{\circ}C \end{array} $			-100	μΑ
OUTPUT	CONTROL (Figure 6)				•		•
V _{OCL}	Output Control Voltage Required for Single Ended or Parallel Output Operation					0.4	٧
V _{OCH}	Output Control Voltage Required for Push-Pull Operation			2.4			٧
TOTAL D	EVICE						
Icc	Standby Power Supply Current				6.0	10	mA
OUTPUT	AC CHARACTERISTICS Use Rec	ommended Operating	Conditions with $T_A = 25^{\circ}C$				
t _r	Rise Time of Output Voltage Common Emitter Configuration (Figure 3)				100	200	ns
	Emitter Follower Configuration (Figure 4)				100	200	
t _f	Fall Time of Output Voltage Common Emitter Configuration (Figure 3)				25	100	ns
	Emitter Follower Configuration (Figure 4)				40	100	

Note 1: $T_{J Max} = 150^{\circ}C$ for the Molded DIP, and 175°C for the Ceramic DIP.

Note 2: Ratings apply to ambient temperature at 25°C. Above this temperature, derate the 16L-Ceramic DIP at 10 mW/°C, and the 16L-Molded DIP at 8.3 mW/°C.

Note 3: Selected devices with tightened tolerance reference voltage available.

Note 4: These limits apply when the voltage measured at Lead 3 is within the range specified.

Functional Description

The basic oscillator (switching) frequency is controlled by an external resistor (R_T) and capacitor (C_T). The relationship between the values of R_T , C_T and frequency is shown in Figure 10.

The level of the sawtooth wave form is compared with an error voltage by the pulse width modulated comparator. The output of the PWM Comparator directs the pulse steering flip-flop and the output control logic.

The error voltage is generated by the error amplifier. The error amplifier boosts the voltage difference between the output and the 5.0V internal reference. See *Figure 7* for error amp sensing techniques. The second error amp is typically used to implement current-limiting.

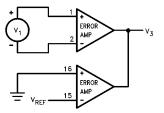
The output control logic selects either push-pull or single-ended operation of the output transistors (see *Figure 6*).

The dead time control prevents on-state overlap of the output transistors as can be seen in *Figure 5*. The dead time is approximately 3.0% or 5.0% of the total period if the dead time control is grounded. This dead time can be increased by connecting the dead time control to a voltage up to 5.0V.

The frequency response of the error amps (Figure 11) can be modified by using external resistors and capacitors. These components are typically connected between the compensation terminal and the inverting input of the error amps.

The switching frequency of two or more LM494 circuits can be synchronized. The timing capacitor, C_T , is connected as shown in Figure 8. Charging current is provided by the master circuit. Discharging is through all the circuits slaved to the master. R_T is required only for the master circuit.

Test Circuits



 $$^{\rm TL/H/10056-3}$$ FIGURE 1. Error Amplifier Test Circuit

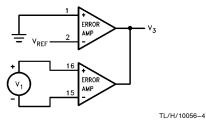
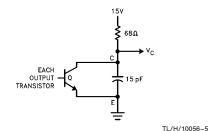


FIGURE 2. Current Limit Sense
Amplifier Test Circuit



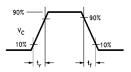
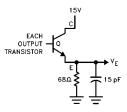
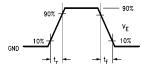


FIGURE 3. Common Emitter Configuration
Test Circuit and Waveform

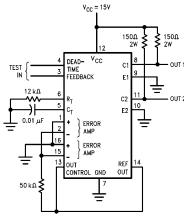


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FIGURE 4. Emitter Follower Configuration Test Circuit and Waveform



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FIGURE 5. Dead Time and Feedback Control Test Circuit

Typical Applications



FIGURE 6. Output Connections for Single Ended and Push-Pull Configurations

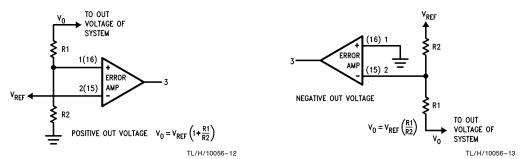


FIGURE 7. Error Amplifier Sensing Techniques

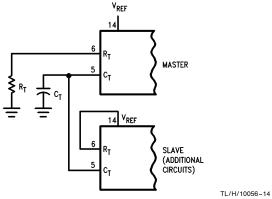


FIGURE 8. Slaving Two or More Control Circuits

Typical Applications (Continued)

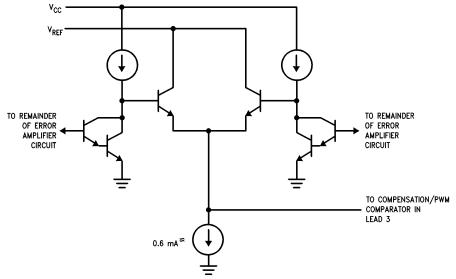


FIGURE 9. Error Amplifier and Current Limit Sense Amplifier Output Circuits TL/H/10056-15

Typical Performance Characteristics

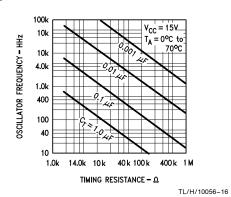
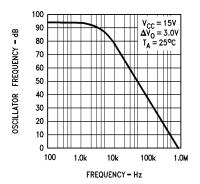
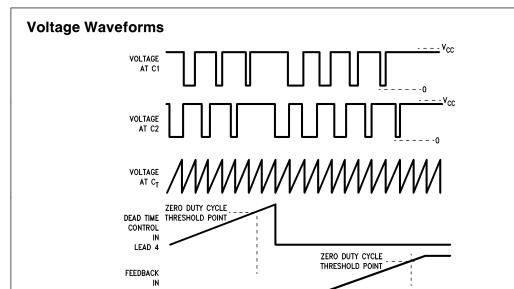


FIGURE 10. Oscillator Frequency vs Timing Resistance



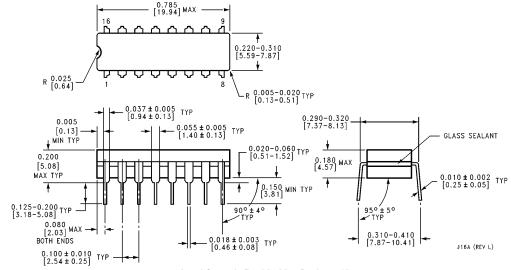
TL/H/10056-17 FIGURE 11. Amplifier Voltage Gain vs Frequency



TL/H/10056-18

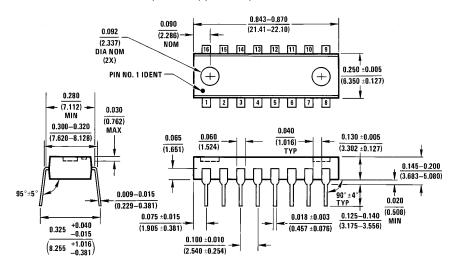
Physical Dimensions inches (millimeters)

LEAD 3



16-Lead Ceramic Dual-In-Line Package (J) Order Number LM494CJ NS Package Number J16A

Physical Dimensions inches (millimeters) (Continued)



16-Lead Molded Dual-In-Line Package (N) Order Number LM494CN or LM494IN NS Package Number N16A

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- A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

N16A (REV.E)



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